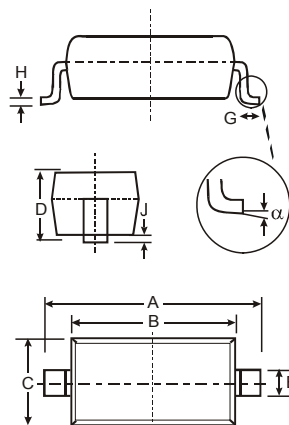


Features

- Total power dissipation: Max. 500 mW.
- Low Zener Impedance.
- High Stability and High Reliability.



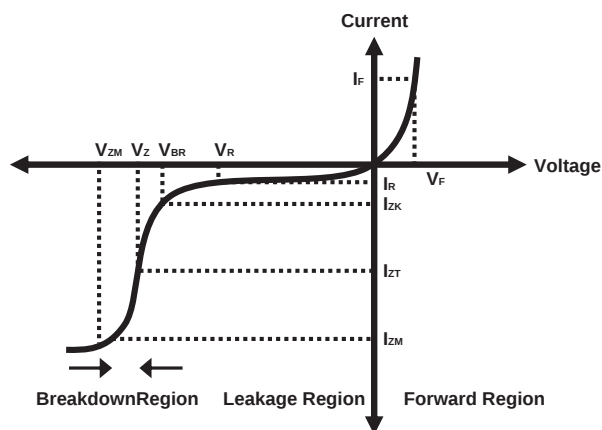
SOD-123		
Dim	Min	Max
A	3.55	3.85
B	2.55	2.85
C	1.40	1.70
D	—	1.35
E	0.45	0.65
	0.55 Typical	
G	0.25	—
H	0.11 Typical	
J	—	0.10
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 65 to + 150	$^\circ\text{C}$
Thermal Resistance Junction to Ambient Air	$R_{\theta\text{JA}}$	400	$^\circ\text{C/W}$
Forward Voltage at $I_F = 10 \text{ mA}$	V_F	0.9	V

- 1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²
- 2) Short duration test pulse used to minimize self-heating effect
- 3) f=1KHz

Zener I vs. V Characteristics



- V_{BR} : Voltage at I_{ZK}
- I_{ZK} : Test current for voltage V_{BR}
- Z_{ZK} : Dynamic impedance at I_{ZK}
- I_{ZT} : Test current for voltage V_Z
- V_Z : Voltage at current I_{ZT}
- Z_{ZT} : Dynamic impedance at I_{ZT}
- I_{ZM} : Maximum steady state current
- V_{ZM} : Voltage at I_{ZM}

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Device	Marking	Zener Voltage Range				Maximum Zener Impedance ³⁾			Maximum Reverse Current		Typical Temperature coefficient @ IZTC=mV/°C		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR	Min	Max	
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	μA	V			
BZT52C2V0	WY	2.0	1.80	2.15	5	150	600	1.0	100	1.0	-3.5	0	5
BZT52C2V4	WX	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52C2V7	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52C3V0	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52C3V3	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52C3V6	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52C3V9	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V3	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52C4V7	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52C5V1	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52C5V6	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52C6V2	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52C6V8	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52C7V5	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52C8V2	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52C9V1	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52C10	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52C11	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52C12	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52C13	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52C15	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52C16	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52C18	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52C20	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52C22	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52C24	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52C27	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52C30	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52C33	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52C36	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52C39	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52C43	WU	43	40.0	46.0	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52C47	WV	47	44.0	50.0	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52C51	WW	51	48.0	54.0	2	125	750	1.0	0.1	38.0	10.0	12.0	5
BZT52C56	XW	56	52.0	60.0	2	135	700	1.0	0.1	39.0	10.0	12.0	5
BZT52C62	6E	62	58.0	66.0	2	200	1000	1.0	0.2	47.0	10.0	12.0	5
BZT52C68	6F	68	64.0	72.0	2	250	1000	1.0	0.2	52.0	10.0	12.0	5
BZT52C75	6H	75	70.0	79.0	2	300	1000	1.0	0.2	57	10.0	12.0	5

TYPICAL TRANSIENT CHARACTERISTICS

FIG 1 Typical Forward Characteristics

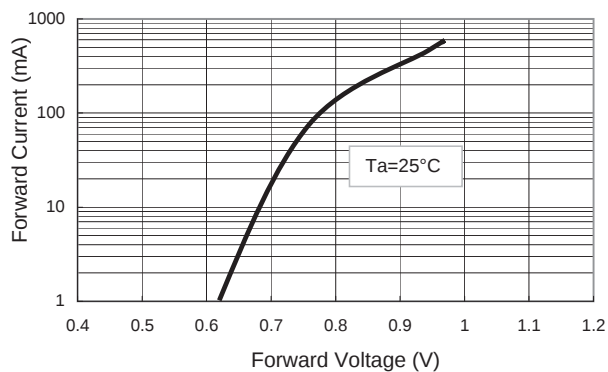


FIG 2 Zener Breakdown Characteristics

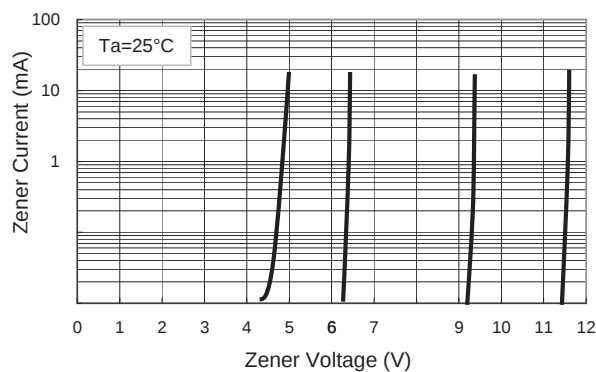


FIG 3 Zener Breakdown Characteristics

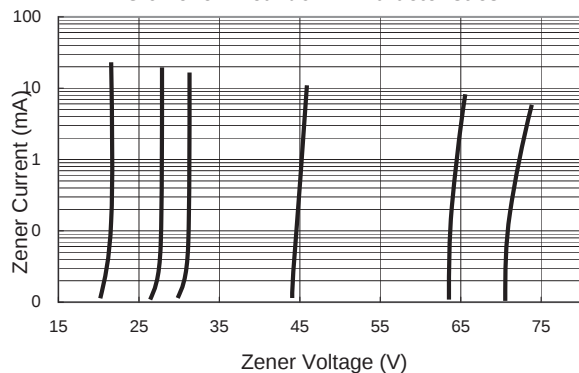


FIG 4 Admissible Power Dissipation Curve

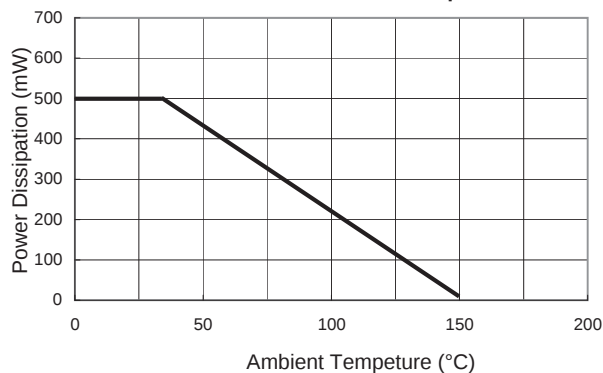


FIG 5 Typical Capacitance

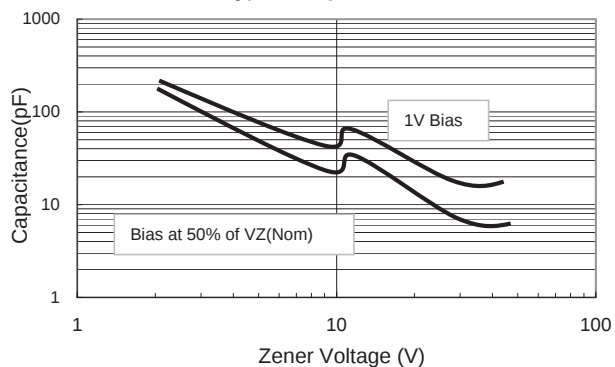
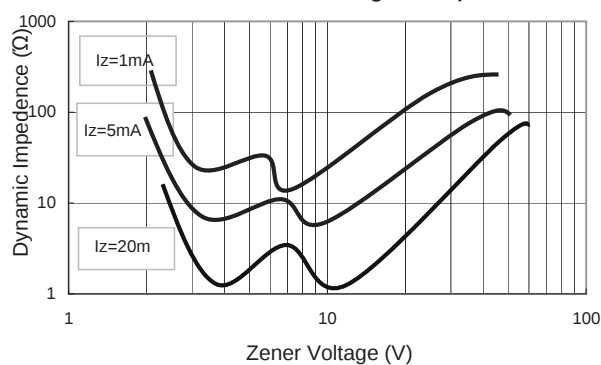


FIG 6 Effect of Zener Voltage on Impedance



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